MOSFET - Power, Dual N-Channel

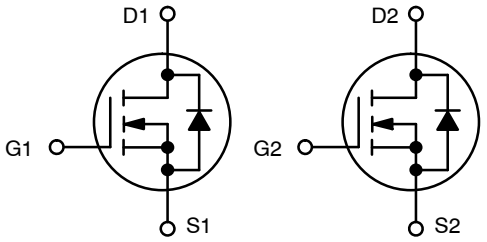
100 V, 10.4 mΩ, 61 A

NVMFD010N10MCL

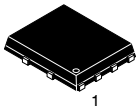
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
100 V	10.4 mΩ @ 10 V	61 A
	14.6 mΩ @ 4.5 V	

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC−Q101 Qualified and PPAP Capable
- NVMFWD010N10MCL − Wettable Flank Products
- These Devices are Pb−Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

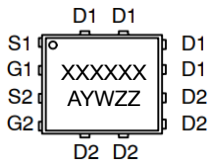


DUAL N−CHANNEL



DFN8 5x6 (SO8FL) CASE 506BT

MARKING DIAGRAM



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	100	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	T_C = 25°C	I_D	61	A
		T_C = 100°C		43	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	84	W
		T_C = 100°C		42	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	11.6	A
		T_A = 100°C		8.2	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25°C	P_D	3.1	W
		T_A = 100°C		1.5	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	270	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	65	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 3.3 A)			E_{AS}	485	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Note 1)	$R_{\theta JC}$	1.79	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	49	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using 1 in^2 pad size, 2 oz. Cu pad.

ORDERING INFORMATION

Device	Package	Shipping†
NVMFD010N10MCLT1G	DFN8 (Pb−Free)	1500 / Tape & Reel
NVMFWD010N10MCLT1G (Wettable Flanks)		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

© Semiconductor Components Industries, LLC, 2021

Downloaded from Arrow.com.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		100			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			50.2		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 100 V	T_J = 25°C			1.0	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 97 μA		1		3	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−5.6		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 17 A			8.7	10.4	mΩ
		V_{GS} = 4.5 V, I_D = 14 A			11.7	14.6	
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 17 A			60		S
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 50 V			1800		pF
Output Capacitance	C_{OSS}				700		
Reverse Transfer Capacitance	C_{RSS}				9.5		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 50 V, I_D = 14 A			12		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 50 V, I_D = 17 A			26		
Threshold Gate Charge	$Q_{G(TH)}$				2.4		
Gate−to−Source Charge	Q_{GS}				4.9		
Gate−to−Drain Charge	Q_{GD}				2.7		
Plateau Voltage	V_{GP}				2.7		V
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 50 V, I_D = 17 A, R_G = 6 Ω			11		ns
Rise Time	t_r				4.2		
Turn−Off Delay Time	$t_{d(OFF)}$				32		
Fall Time	t_f				5.5		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 17 A	T_J = 25°C		0.85	1.3	V
			T_J = 125°C		0.74		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 9 A			40		ns
Reverse Recovery Charge	Q_{RR}				31		nC
Charge Time	t_a				19		ns
Discharge Time	t_b				21		nS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

Downloaded from Arrow.com.

TYPICAL CHARACTERISTICS

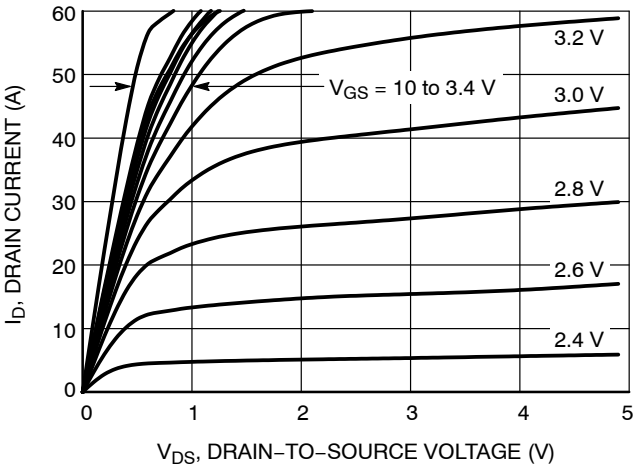


Figure 1. On−Region Characteristics

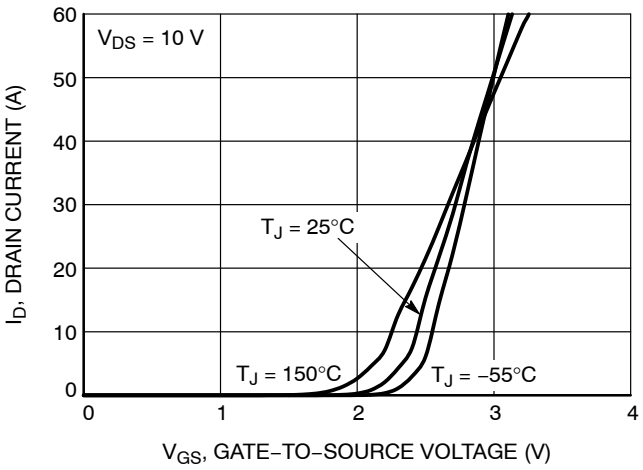


Figure 2. Transfer Characteristics

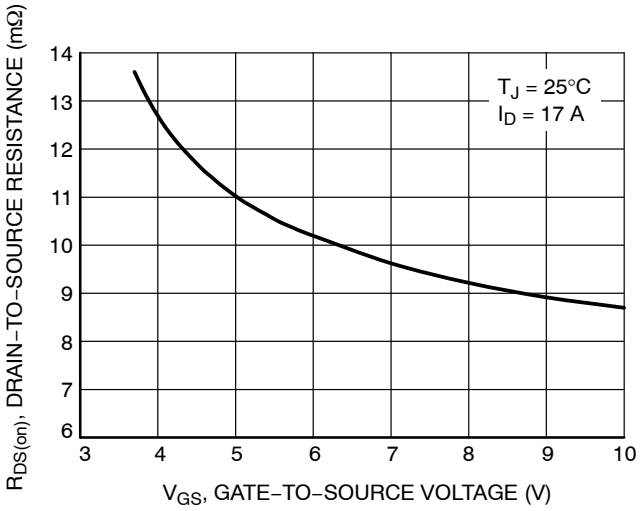


Figure 3. On−Resistance vs. Gate−to−Source Voltage

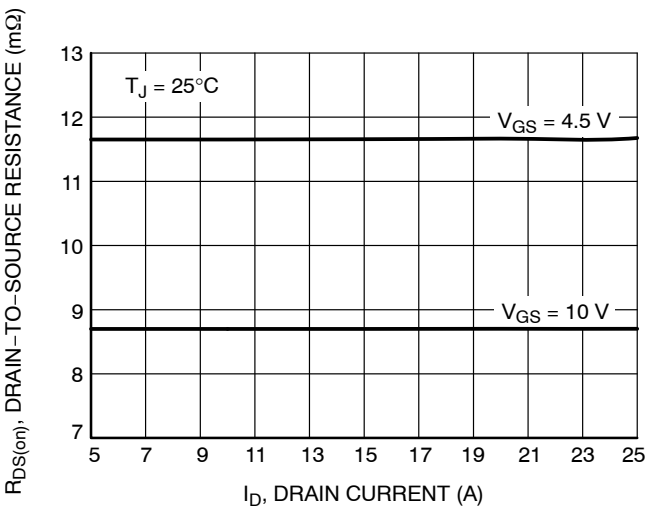


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

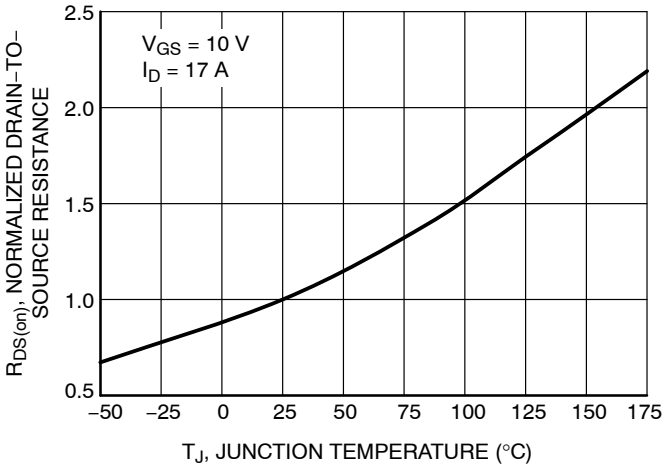


Figure 5. On−Resistance Variation with Temperature

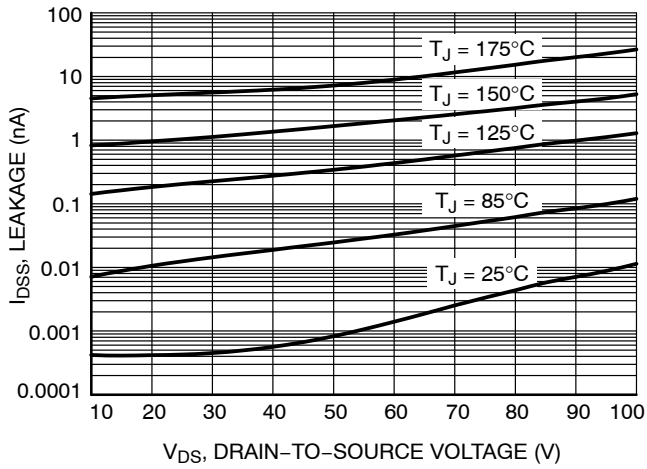


Figure 6. Drain−to−Source Leakage Current vs. Voltage

Downloaded from Arrow.com.

TYPICAL CHARACTERISTICS

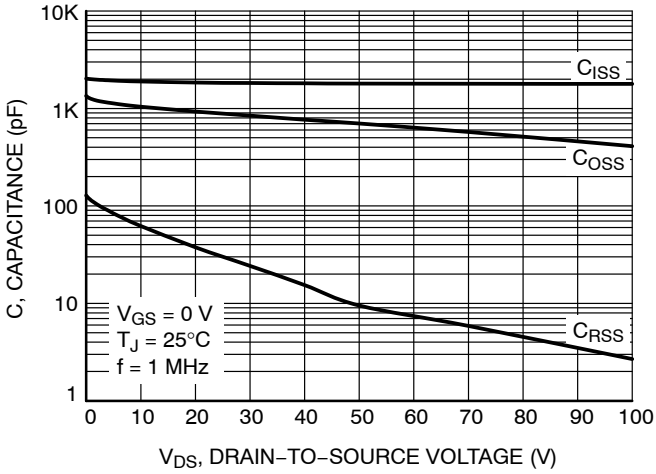


Figure 7. Capacitance Variation

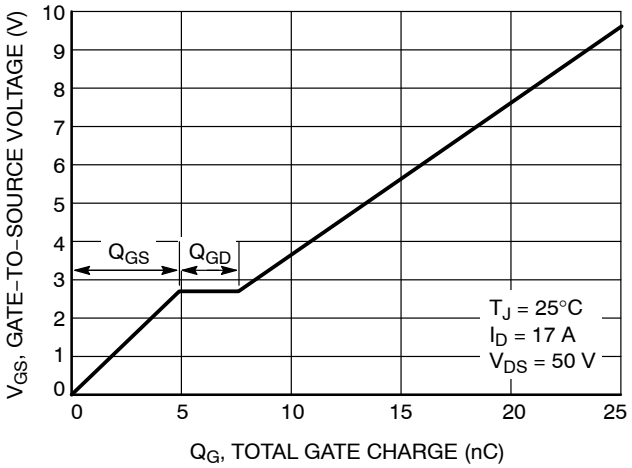


Figure 8. Gate−to−Source Voltage vs. Total Charge

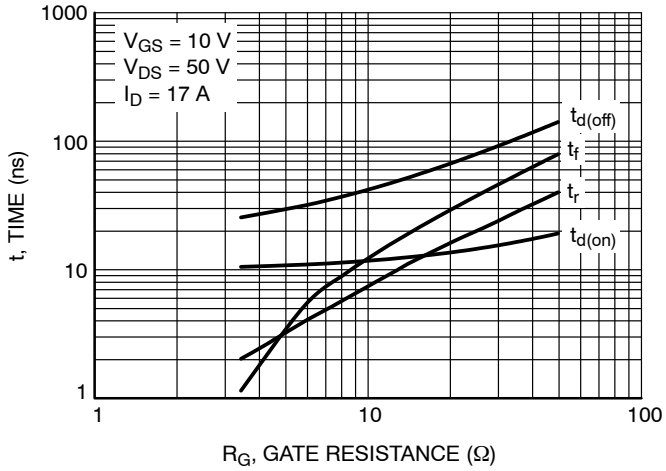


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

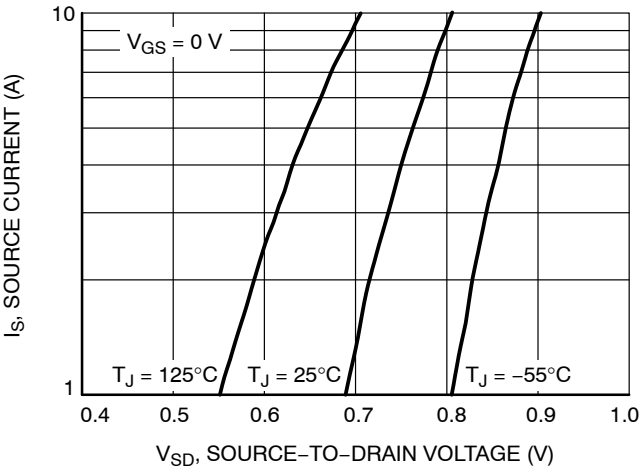


Figure 10. Diode Forward Voltage vs. Current

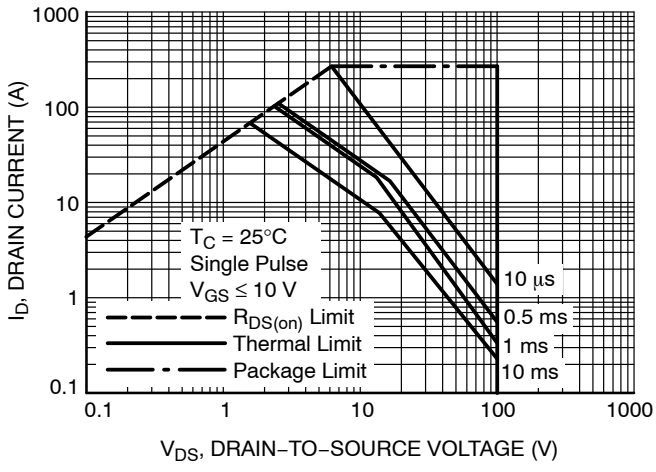


Figure 11. Maximum Rated Forward Biased Safe Operating Area

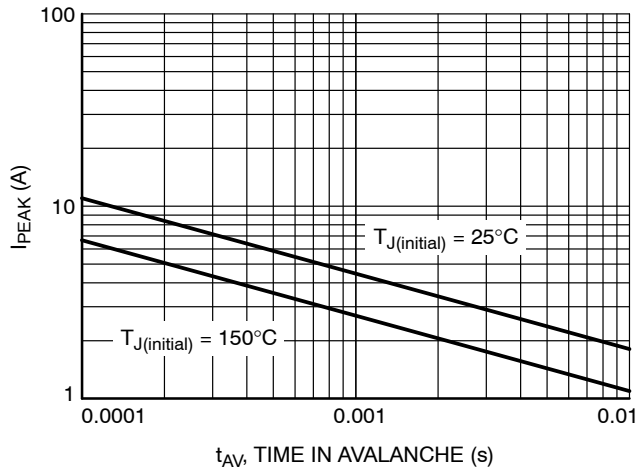


Figure 12. Maximum Drain Current vs. Time in Avalanche

Downloaded from Arrow.com.

TYPICAL CHARACTERISTICS

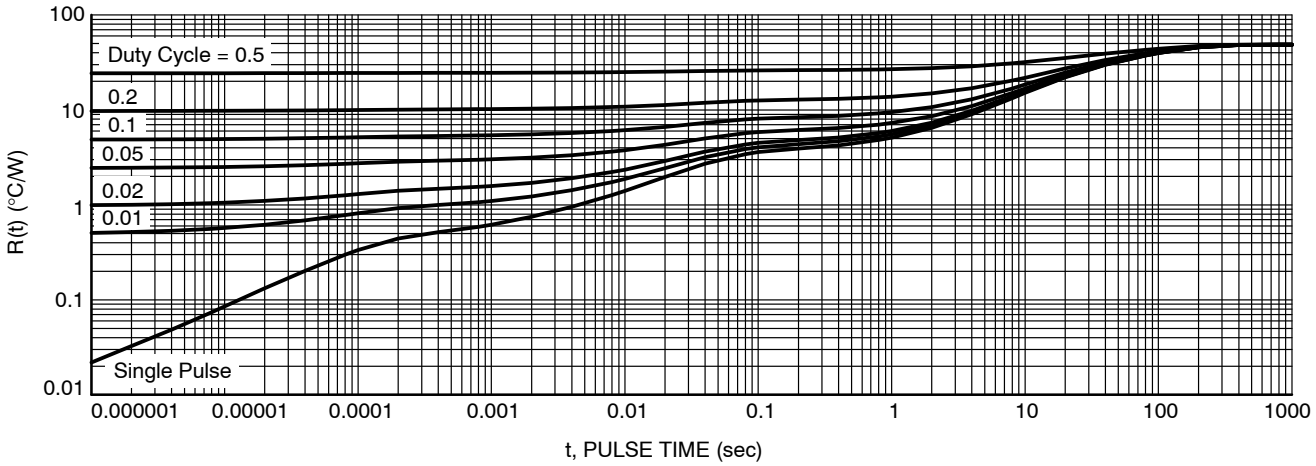
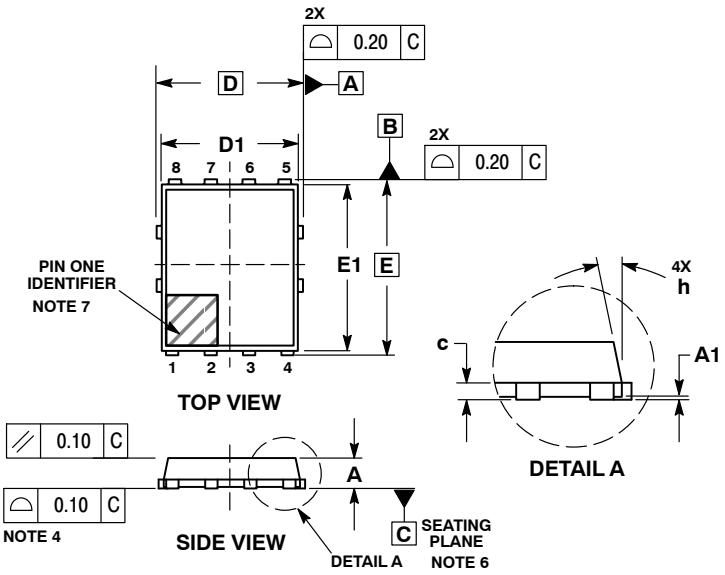


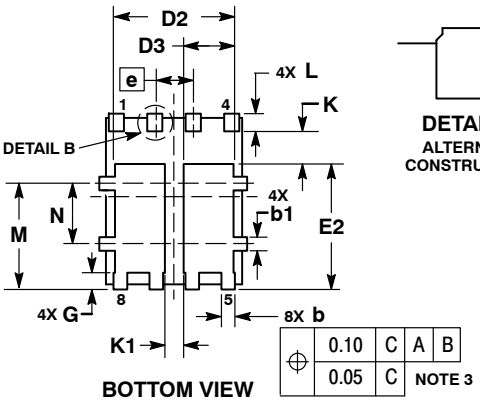
Figure 13. Transient Thermal Impedance

Downloaded from Arrow.com.

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P Dual Flag (SO8FL−Dual)
CASE 506BT
ISSUE E

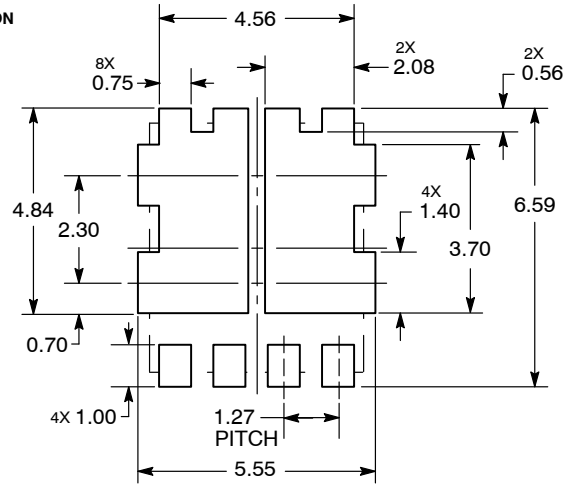




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. PROFILE TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
7. A VISUAL INDICATOR FOR PIN 1 MUST BE LOCATED IN THIS AREA.

	MILLIMETERS		
DIM	MIN	MAX	MAX
A	0.90	---	1.10
A1	---	---	0.05
b	0.33	0.42	0.51
b1	0.33	0.42	0.51
c	0.20	---	0.33
D	5.15 BSC		
D1	4.70	4.90	5.10
D2	3.90	4.10	4.30
D3	1.50	1.70	1.90
E	6.15 BSC		
E1	5.70	5.90	6.10
E2	3.90	4.15	4.40
e	1.27 BSC		
G	0.45	0.55	0.65
h	---	---	12 °
K	0.51	---	---
K1	0.56	---	---
L	0.48	0.61	0.71
M	3.25	3.50	3.75
N	1.80	2.00	2.20

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Downloaded from Arrow.com.

onsemi, onsemi , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi's** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊

Downloaded from Arrow.com.